

Attorney's Docket No.:07977/213002

In the Specification:

Please replace the paragraph beginning on page 29 line 29
with the following new paragraph:

D¹
What is shown in Fig. 12 is a diagram showing a part of a buffer circuit section within a source driver circuit in a liquid-crystal display device. In particular, this figure shows an end portion of the buffer circuit section, in which two ~~inverter~~ inverter circuits 1201 and 1202 are disposed on an endmost portion, and the same circuits and nickel added regions are cyclically arranged on a lower side of the figure. An equivalent circuit diagram of Fig. 12 is shown in Fig. 13.

Please replace the paragraph beginning on page 30 line 8
with the following new paragraph:

D²
The characteristics of the TFT that constitutes ~~inverter~~ inverter circuits (for example, 1203, 1204 and so on) fabricated under the nickel added region 1212 are sufficient. This is because since they are disposed between the respective nickel added regions, a distance of crystal growth of the silicon film in the region therebetween is sufficient.

Please replace the paragraph beginning on page 30 line 14
with the following new paragraph:

Attorney's Docket No.: 07977/213002

D3
On the other hand, the ~~inverter~~ inverter circuits 1201 and 1202 are circuits disposed on the endmost portion, and in order to obtain a sufficient characteristic of the TFTs that constitute those circuits, a dummy nickel added region 1211 is disposed as shown in Fig. 12.

Please replace the paragraph beginning on page 30 line 18 with the following new paragraph:

D4
In particular, an object of this embodiment is to obtain a sufficient characteristic of the TFT that constitutes the ~~inverter~~ inverter circuit 1201 which is disposed on the endmost portion. This is because in the case where crystal growth is insufficient, the characteristic of the above TFT is most deteriorated.

Please replace the paragraph beginning on page 30 line 24 with the following new paragraph:

D5
Since the dummy nickel added region 1211 is disposed as mentioned above, the distance of crystal growth of the silicon film in the regions where the TFTs that constitute the ~~inverter~~ inverter circuits 1201 and 1202 are disposed is made sufficiently long, thereby being capable of obtaining a sufficient characteristic of the TFTs.

Attorney's Docket No.:07977/213002

Please replace the paragraph beginning on page 30 line 28
with the following new paragraph:

D6 The, the operating speed of the ~~inverter~~ inverter circuits
1201 and 1202 which are disposed on the endmost portion can be
sufficiently increased.

Please replace the paragraph beginning on page 30 line 30
with the following new paragraph:

D7 Furthermore, the characteristic of the TFTs that constitute
the ~~inverter~~ inverter circuits 1201 and 1202 is made identical
with the characteristic of the TFT that constitutes the ~~inverter~~
inverter circuit fabricated under the nickel added region 1202,
thereby being capable of obtaining a plurality of buffer
circuits having substantially the same operating speed.
